

IN THE SPECIFICATION

Please amend the indicated portions of the specification as follows:

[0028] In the light sensor circuit, once the drain voltage VD of the MOS type transistor Q1 was switched over to the low level L for initializing the circuit, the transistor Q1 is brought into the low-resistance state if a potential between the gate voltage VG and the drain voltage VD is greater than a threshold of the transistor Q1. Therefore, the source side potential at that moment becomes equal to the drain voltage VD (a difference between potentials still remains in practice), causing the junction parasitic capacity C of the photodiode [[C]] PD to be discharged.

[0031] Figure 4 schematically illustrates the operation of the light sensor circuit by a flow of electric charge q of the transistor Q1 when detecting a light signal. The junction parasitic capacity C of the photodiode PD is discharged for initializing the light sensor circuit before detecting a light signal and then charged. In this case, the output voltage Vpd (a terminal voltage of the photodiode PD) with an elapse of a specified time from the initializing timing becomes a value corresponding to the quantity of incident light Ls. In other words, the light sensor circuit after initialization can obtain a discharging characteristic with a specified time constant in response to a change in the quantity of incident light.